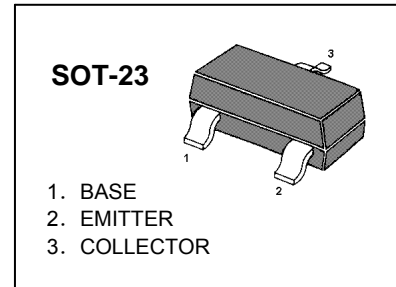


## 2SC1623 TRANSISTOR(NPN)

### FEATURE

- ◆ High DC current gain :  $h_{FE}=200(\text{Typ})V_{CE}=6V, I_C=1\text{mA}$
- ◆ High voltage:  $V_{CEO}=50V$



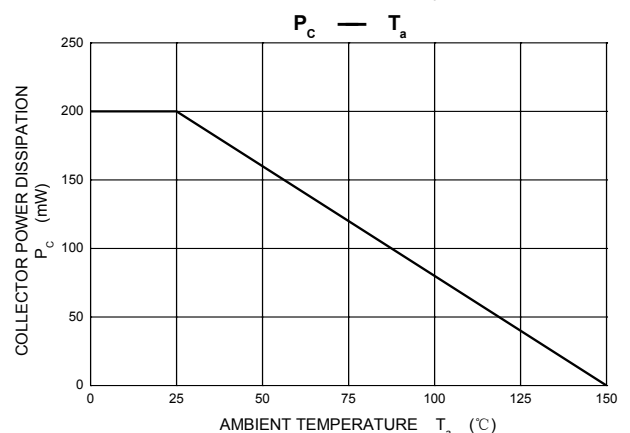
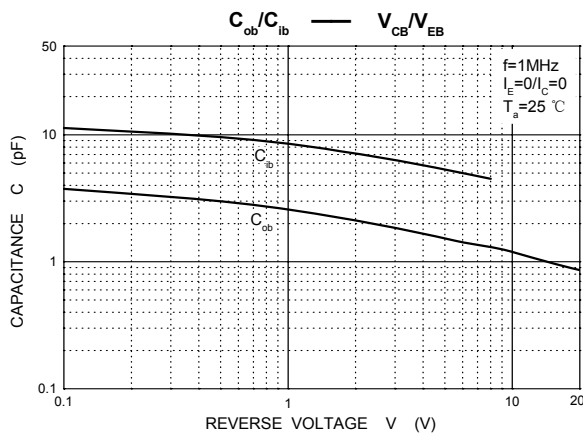
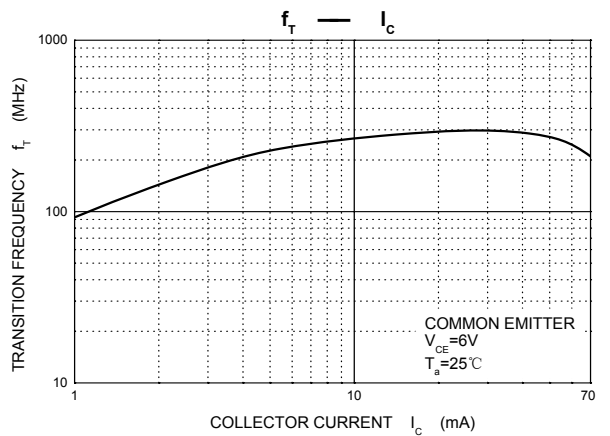
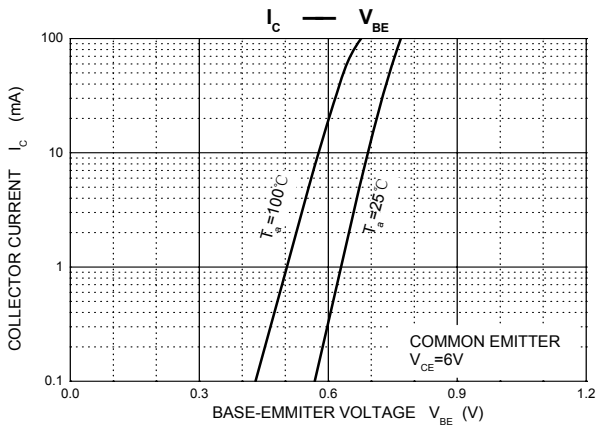
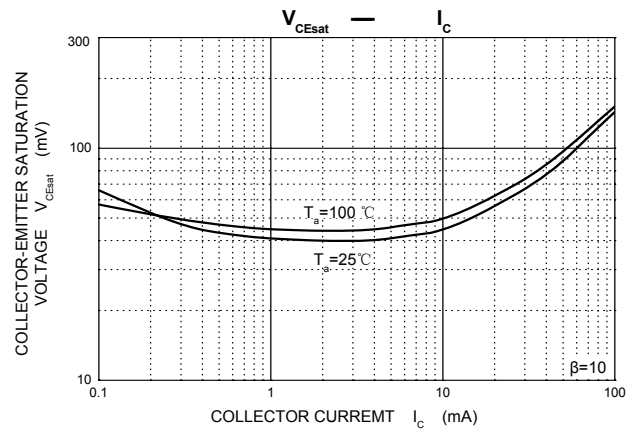
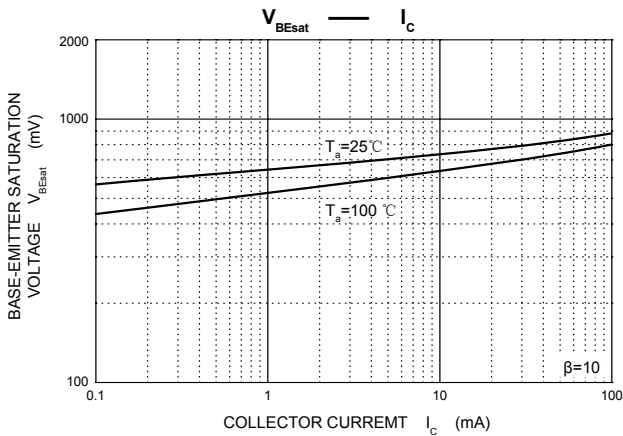
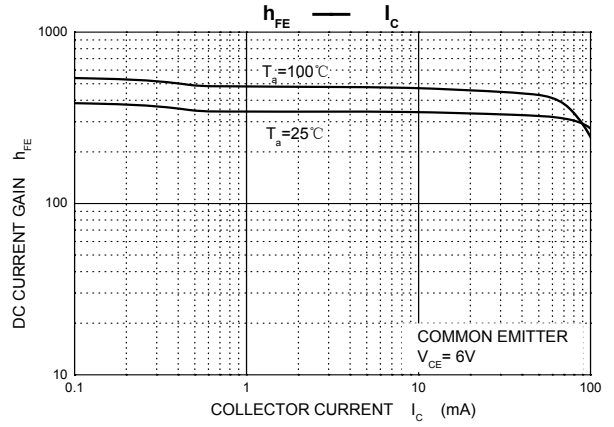
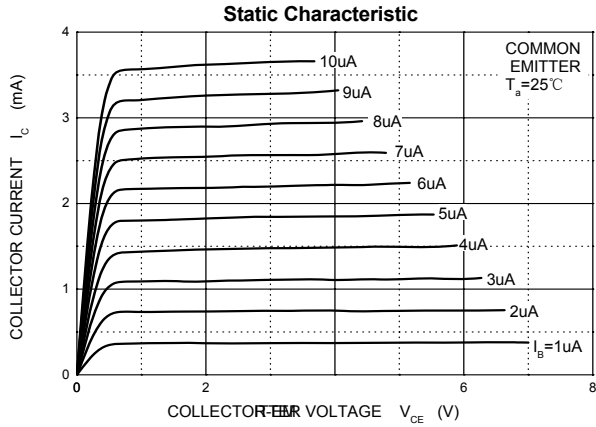
### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	100	mA
$P_C$	Collector Power Dissipation	200	mW
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test condition	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=6V, I_C=1\text{mA}$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=10\text{mA}$		250		MHz

TYPICAL CHARACTERISTICS



**PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT-23

